Preparation and Application of Chemically Functionalized Graphene

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Hersam Group Graphene Research: Dispersions



Hersam Group Graphene Research: Applications



Today's Talk: Graphene Surface Chemistry



Novoselov et al., *PNAS* **102**, 10451 (2005) Neto et al., *Rev. Mod. Phys.* **81**, 109 (2009)

- The superlative and exotic electronic properties of graphene have been widely studied in condensed matter physics.
- However, to realize its full potential for electronic applications, interfaces with other materials will need to be precisely controlled.
- In addition to serving as a seeding layer for materials growth, chemical functionalization of graphene holds promise for tailoring electronic properties (e.g., doping, band gap control, etc.).



Past Work: Silicon Surface Chemistry

APL, 85, 2619 (2004); Nano Lett., 4, 55 (2004); PNAS, 102, 8838 (2005); PRL, 97, 187601 (2006).



Single molecule characterization



1-D heteromolecular nanostructures



Cryogenic STM spectroscopy



Current-driven molecular motion





Current-driven molecular desorption Hersam Group

Outline

<u>Review Article</u>: *MRS Bulletin*, **36**, 532 (2011).



- Weakly interacting organic monolayers on graphene
 - PTCDA
 - Seeding layer for ALD
- Strongly interacting organic and inorganic adsorbates on graphene
 - PTCDI-C8
 - Organic free radicals
 - Atomic oxygen
- Nanopatterning on graphene
 - Nanoscale oxidation
 - Molecular heterostructures

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Preparation and UHV STM of Epitaxial Graphene

Applied Physics Letters, 96, 143103 (2010).



- SiC(0001) graphitized by annealing in UHV at ~1350°C
- Defect density and relative amount of SLG, BLG, and 6√3 depend on the details of the UHV processing
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Surface Chemistry of Epitaxial Graphene

Review Article: MRS Bulletin, 36, 532 (2011).



- Substrate: n-type SiC(0001)
- Graphitized by repeated annealing in UHV at ~1350°C for 30 s
- Preparation conditions were chosen to yield a variety of surface defects to determine their influence on subsequent chemistry



PTCDA

(3,4,9,10-perylene-tetracarboxylic acid dianhydride)

Nature Chemistry, 1, 206 (2009).



- Perylene-based molecule that forms ordered adlayers on graphite via noncovalent bonding (preserves sp² hybridization of graphene)
- Thermally stable \rightarrow amenable to gas phase processing
- Crystalline molecular semiconductor that has been widely studied for organic thin film device applications



PTCDA Monolayer on Epitaxial Graphene

Nature Chemistry, 1, 206 (2009).



June, 2009

- Gas phase deposition of a monolayer of PTCDA
- Stable herringbone phase achieved at room temperature
- Long range order is observed including seamless continuity in molecular ordering over step edges



Insensitivity to Defects

Nature Chemistry, 1, 206 (2009).



- Ordering of the PTCDA monolayer is unperturbed by onedimensional and point defects in the substrate
- Suggests that intermolecular interactions are more important than molecule-substrate interactions



PTCDA Growth Beyond One Monolayer

Surface Science, 605, 1685 (2011).



- Layer-by-layer growth for the first 2 monolayers
- Thicker films transition to Stranski-Krastanov growth



Submonolayer Coverage

Nature Chemistry, 1, 206 (2009).



- Stable islands of PTCDA are observed at submonolayer coverage at room temperature
- Enables direct comparison between PTCDA and clean graphene
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Tunneling Spectroscopy on PTCDA/Graphene

Nature Chemistry, 1, 206 (2009).



Tunneling spectra reconfirm weak interaction between PTCDA and graphene (i.e., PTCDA imparts chemical functionality with minimal electronic perturbation) NU

Chemical Robustness of the PTCDA Monolayer

Nature Chemistry, 1, 206 (2009).

Before Ambient Exposure

After Ambient Exposure



- Monolayer is brought out into ambient laboratory air for several minutes; then reintroduced to UHV and degassed
- Monolayer remains intact and pristine at the molecular scale, suggesting its use as a template for subsequent chemistry



Seeding Atomic Layer Deposition on Graphene



• Monolayer of PTCDA can seed ALD growth of dielectrics on graphene

• Other gas phase and liquid phase chemistries are under development

10nm Al₂O₃ on PTCDA-Graphene

ACS Nano, 5, 5223 (2011).



- Even after 10 nm of AI_2O_3 , ALD film uniformity is maintained across the surface of PTCDA functionalized graphene.
- Synchrotron X-ray reflectivity reveals no measurable change in the underlying graphene following PTCDA-seeded ALD.



Superior Adhesion Provided by PTCDA



- Even under minimal contact forces (~10 nN), contact mode AFM scratches off Al₂O₃ (~2nm) from pristine graphene
- Al₂O₃ (~2nm) on PTCDA-Graphene is unperturbed by contact mode AFM
- Similar results have been achieved for HfO₂

Atomic Layer Deposition of HfO₂





• Improved conformality for ALD hafnia on PTCDA/graphene



Metal/Oxide/Graphene Capacitor Structures



- Dielectric structure: PTCDA + 3 nm ALD AI_2O_3 + 10 nm ALD HfO_2
- AFM and SEM confirm highly conformal growth of dielectric stack

Metal/Oxide/Graphene Electrical Measurements





- Low pinhole density and leakage current for 100 µm test structures
- Capacitance measurement implies $k_{alumina} = 5.6$ and $k_{hafnia} = 13$
- Low hysteresis suggests low interface trap density



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PTCDI-C8 Monolayers on Epitaxial Graphene

Nano Letters, 11, 589 (2011).

N,N'-dioctyl-3,4,9,10-perylenedicarboximide (PTCDI-C8)



 Self-assembled monolayers of PTCDI-C8 on epitaxial graphene show different ordering than PTCDA Hersam Group

Defect Interactions with PTCDI-C8

Nano Letters, **11**, 589 (2011).



- Unlike PTCDA, PTCDI-C8 ordering is interrupted by defects
- Smaller defects are surrounded by PTCDI-C8; larger defects can affect formation of new domains
- Intermolecular forces in PTCDI-C8 monolayer likely weaker than in PTCDA monolayer



Chemical Robustness of the PTCDI-C8 Monolayer

Nano Letters, **11**, 589 (2011).



After 12 hr ambient exposure



- PTCDI-C8 monolayer was brought out into ambient laboratory air for 12 hours, then reintroduced to UHV and degassed
- Monolayer ordering and cleanliness are maintained



Covalent Chemistry on Epitaxial Graphene

JACS 1992, 114, 5883; Chem. Mater. 2006, 18, 2021; JACS 2009, 131, 1336.

Reaction scheme for aryldiazonium salt:



- Covalent functionalization of graphene recently demonstrated via reduction of aryldiazonium salt in solution
- Disruption of graphene sp² hybridization influences electronic properties
- Radical mediated chemistry may lead to polymerization



UHV STM of Covalently Arylated Graphene

Journal of the American Chemical Society, **132**, 15399 (2010).

SiC-graphene dipped into 4-nitrophenyldiazonium salt solution in glove box followed by degassing at 500°C in UHV





- Strong evidence for polymerization
- Robust in atmosphere
- Local perturbation to electronic properties at covalent binding sites



STS on Covalently Arylated Bilayer Graphene

Journal of the American Chemical Society, **132**, 15399 (2010).



Clean bilayer graphene shows a minimum in dl/dV at -0.3 V (i.e., n-type)

 On the arylated surface, the minimum at -0.3 V is not observed but finite dl/dV is still present at all biases

 In a small number of cases (~ 5%), a band gap is observed on the arylated surface (presumably at covalent binding sites)



Covalently Modifying Graphene with Atomic Oxygen

Nature Chemistry, 4, 305 (2012).



 Atomic oxygen is generated in UHV by cracking molecular oxygen on a hot (~1500°C) tungsten filament.

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• Bright protrusions are attributed to chemisorbed oxygen species.



High Resolution STM and Density Functional Theory

Nature Chemistry, 4, 305 (2012).



• Uniformity of features in STM implies one primary binding configuration.

• Comparison with DFT calculations suggests epoxy functionalization.

Reversible UHV Oxidation and Reduction

Nature Chemistry, 4, 305 (2012).



Oxidation is fully reversible upon thermal annealing or STM lithography.
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X-Ray Photoelectron Spectroscopic Verification

Nature Chemistry, 4, 305 (2012).



- O1s peak clearly illustrates the reversibility of the UHV oxidation process.
- C1s shoulder at 286.3 eV is indicative of epoxy functionalization.

Raman and Ultraviolet Photoelectron Spectroscopy



• Raman: D/2D ratio increases after oxidation and reduces following anneal.

• <u>UPS</u>: Electronic density of states decreases after oxidation and increases following anneal, suggesting modification of the electronic band structure.

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Nanoscale Oxidation with cAFM

Nano Letters, 5, 91 (2005).



Local anodization of silicon surfaces via conductive atomic force microscopy (cAFM) in ambient conditions



Nanoscale Oxidation of Graphene with cAFM

Advanced Materials, 23, 2181 (2011).



Controllable nanoscale patterns generated on epitaxial graphene under ambient conditions using conductive AFM Hersam Group



Nanopattern Growth Kinetics

Advanced Materials, 23, 2181 (2011).



- The kinetics data show distinct regimes of nanopattern height variation with growth conditions.
- The observed distinct regimes are attributed to the non-homogenous depth profile of epitaxial graphene on SiC (i.e., graphene, $6\sqrt{3}$, bulk SiC)



Selective Etching in HF

4.4 nm b a 46 nm 400 nm 400 nm С d Before etch After etch Etch depth (nm) Height (nm) 1.0 0.8 0.6 0.4 0.8 1.2 2.0 2.4 2.8 3.2 0.0 0.4 0.8 1.2 1.6 1.6 Distance (µm) Oxide Height (nm)

Advanced Materials, 23, 2181 (2011).

- HF selectively etches nanopatterns with no apparent damage to graphene.
- Etch depth vs. original height has distinct regimes, again reflecting the layered structure of epitaxial graphene on SiC.

Nanopatterning with UHV STM

Annual Review of Physical Chemistry, 60, 193 (2009).

 Hydrogen on Si(100)
 Cyclopentene on Si(100)

 Image: Sam on Au(111)
 Image: Sam on Au(111)

 Image: Sam on Au(111)
 Image: Sam on Au(111)

- STM can be used to pattern variety of chemical resist layers and isolated molecules
- Tip-induced desorption via electronic excitation or vibrational heating

Nanopatterning PTCDA on Epitaxial Graphene

Nano Letters, **11**, 589 (2011).



- PTCDA can be selectively removed with STM voltage pulsing
- Sub-5 nm features possible but inconsistent, probably due to strong intermolecular forces in the PTCDA monolayer Hersam Group



Feedback Controlled Lithography of PTCDA

Nano Letters, **11**, 589 (2011).



 Control and reproducibility of patterns greatly improved by using feedback controlled lithography to selectively desorb PTCDA domains that are ~2 nm diameter



PTCDA as a Chemical Resist on Graphene



Heteromolecular Nanopatterns on Graphene

Nano Letters, 11, 589 (2011).



- Heteromolecular nanopatterns implemented with PTCDA resist and PTCDI-C8 insert
- Molecular ordering is observed in the PTCDI-C8 nanopatterns



Nanopatterning Covalently Modified Graphene

Journal of the American Chemical Society, **132**, 15399 (2010).



- Aryldiazonium chemistry can also be used as a resist for UHV STM nanopatterning
- Threshold parameters: $V_{sample} = -5 V$; I = 1 nA
- Nanoribbons with sub-5 nm width reproducibly patterned
- Writings parameters have little to no effect on width

Summary



- Noncovalent organic functionalization imparts uniform chemical functionality with minimal perturbation to underlying graphene.
- Radical-mediated chemistry enables covalent grafting to graphene.
- Electron and photon driven nanopatterning has been achieved down to the molecular scale on graphene. Hersam Group



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